

SANYO Semiconductors DATA SHEET

2SA1965-S-

PNP Epitaxial Planar Silicon Transistor

Muting Circuit Applications

Features

- Ultrasmall-sized package permitting applied sets to be made small and slim.
- · Small output capacitance.
- · Low collector-to-emitter saturation voltage.
- · Low ON resistance.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-15	V
Collector-to-Emitter Voltage	VCEO		-10	V
Emitter-to-Base Voltage	VEBO		-5	V
Collector Current	IC		-100	mA
Collector Current (Pulse)	ICP		-200	mA
Base Current	IΒ		-20	mA
Collector Dissipation	PC		150	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Cumbal	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =-12V, I _E =0A			-0.1	μΑ
Emitter Cutoff Current	IEBO	VEB=-4V, IC=0A			-0.1	μΑ
DC Current Gain	hFE	V _{CE} =-2V, I _C =-5mA	200		600	
Gain-Bandwidth Product	fT	V _{CE} =-5V, I _C =-10mA		600		MHz
Output Capacitance	Cob	VCB=-10V, f=1MHz		5.0		pF

Marking: KA

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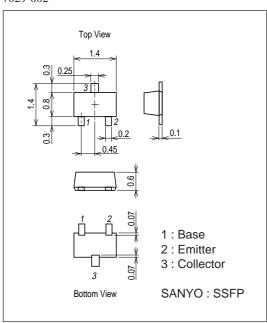
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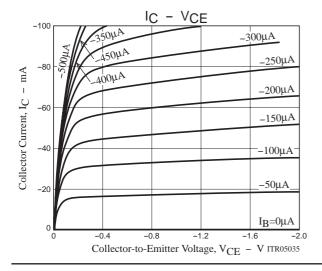
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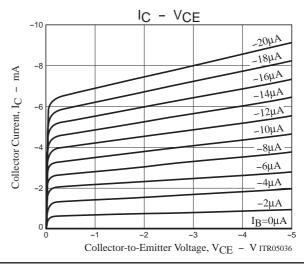
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Oill
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=-10mA, IB=-1mA		-16	-35	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =-10mA, I _B =-1mA		-0.75	-1.1	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =-10μA, I _E =0A	-15			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=-1mA, RBE=∞	-10			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =-10μA, I _C =0A	-5			V
On Resistance	Ron	I _B =-3mA, f=1MHz		1.2		Ω

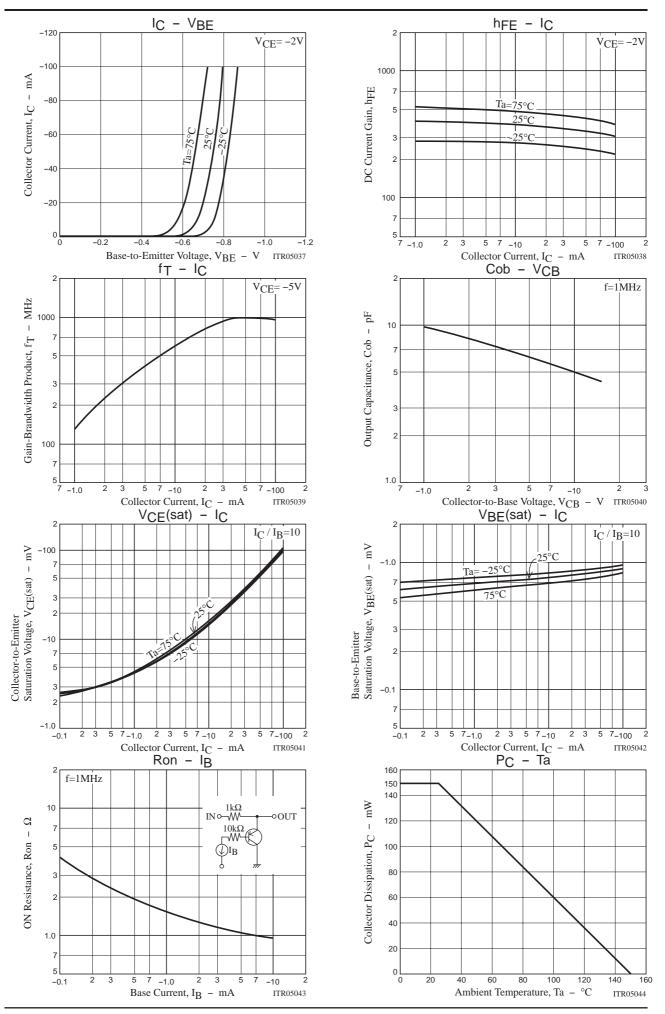
Package Dimensions

unit : mm (typ) 7029-002









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